

Cypress Semiconductor Product Qualification Report

QTP# 071502 VERSION 2.1
August 2008

Ovation 1 Family S4AD-5/C8QR-3R Technology, Fab2/4	
CYONS1001 CYONS1001L CYONS1001G CYONS1001LR CYONS10017 CYONS1001T0 CYONS10800 CYONS10810 CYONS10820	Laser Optical Sensor

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PRODUCT QUALIFICATION HISTORY

QUAL REPORT	DESCRIPTION OF QUALIFICATION PURPOSE	DATE COMP.
071502	CYONS1001 (Laser Optical Sensor) VCSEL and GOOBI Qualification	Aug 07
072206	CYONS1001 (Optical Navigation System) Ovation 1A (New Digital Die – 7CN1200AC) Qualification	Aug 07
080804	CYONS1001 (Optical Navigation Sensor) S4 die Metal Mask (minor change)	Mar 08

Cypress products are manufactured using qualified processes. The technology qualification for this product is referenced above and must be considered to get a complete and thorough evaluation of the reliability of the product.

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose:	CYONS1001 (Laser Optical Sensor) VCSEL and GOOBI Qualification
Marketing Part #:	CYONS1001, CYONS1001L, CYONS1001G, CYONS1001LR, CYONS10017, CYONS1001T0, CYONS10800/10/20
Device Description:	2.7V-3.6V two piece laser optical sensor with integrated source, available in QFN 42L
Cypress Division:	Cypress Semiconductor Corporation – Silicon Light Machine

TECHNOLOGY/FAB PROCESS DESCRIPTION (Analog Die : 7CN0000A)			
Number of Metal Layers:	2	Metal Composition:	Metal 1: 500A Ti / 6000A Al 0.5% Cu / 1200A TiW Metal 2: 500A T i / 8000A Al 0.5% Cu / 300A TiW
Passivation Type and Materials:	7000A TEOS / 6000A Si ₃ N ₄		
Generic Process Technology/Design Rule (μ-drawn):	Single Poly, Double Metal, 0.35 μm		
Gate Oxide Material/Thickness (MOS):	SiO ₂ / 11		
Name/Location of Die Fab (prime) Facility:	Cypress CTI-Texas		
Die Fab Line ID/Wafer Process ID:	Fab2, S4AD-5		

TECHNOLOGY/FAB PROCESS DESCRIPTION (Digital Die: 7CN1001A)			
Number of Metal Layers:	4	Metal Composition:	Metal 1: 300A Ti / 3200A Al 0.5% Cu / 300A TiW Metal 2: 150A Ti / 4000A Al 0.5% Cu / 300A TiW Metal 3: 150A Ti / 4000A Al 0.5% Cu / 300A TiW Metal 4: 150A Ti / 4000A Al 0.5% Cu / 300A TiW
Passivation Type and Materials:	1000A TEOS / 9000A Si ₃ N ₄		
Generic Process Technology/Design Rule (μ-drawn):	CMOS/ 0.3μm		
Gate Oxide Material/Thickness (MOS):	SiO ₂ DGOX 32/55A		
Name/Location of Die Fab (prime) Facility:	Cypress CMI-Minnesota		
Die Fab Line ID/Wafer Process ID:	Fab4, C8Q-3R		

TECHNOLOGY/FAB PROCESS DESCRIPTION (VCSEL)			
Number of Metal Layers:	1	Metal Composition:	Metal 1: Ti: Pt: Au
Passivation Type and Materials:	SiN		
Generic Process Technology/Design Rule (μ-drawn):	Oxide VCSEL		
Gate Oxide Material/Thickness (MOS):	N/A		
Name/Location of Die Fab (prime) Facility:	Bookham/Zurich, Switzerland		
Die Fab Line ID/Wafer Process ID:	N/A		

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY FACILITY SITE
42-Lead QFN	CML Philippines

Note: Package Qualification details available upon request.

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION

Package Designation:	LB42
Package Outline, Type, or Name:	42-lead Quad Flat No Lead (QFN)
Mold Compound Name/Manufacturer:	Sumitomo G700H Type A
Mold Compound Flammability Rating:	V-0 UL-94
Mold Compound Alpha Emission Rate:	N/A
Oxygen Rating Index:	NA
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	NiPdAu (20-80um Ni, 0.8-1.2um Pd, 0.12-0.5um Au)
Die Backside Preparation Method/Metallization:	Backgrind
Die Separation Method:	100% Saw
Die Attach Supplier:	Dexter/Ablestik
Die Attach Material:	QMI 509 - Analog and Digital Die 84-1LMISR4 - VCSEL die
Die Attach Method:	Epoxy Dispensing
Bond Diagram Designation:	001-07289
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au 1.0mil
Thermal Resistance Theta JA °C/W :	30°C/W
Package Cross Section Yes/No:	N/A
Assembly Process Flow:	11-20099
Name/Location of Assembly (prime) facility:	CML
MSL Level:	3
Reflow Profile:	260C

ELECTRICAL TEST / FINISH DESCRIPTION

Test Location:	CML-R
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RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENTS

Stress/Test	Test Condition (Temp/Bias)	Result P/F
Electrostatic Discharge Human Body Model (ESD-HBM)	2200V JEDEC EIA/JESD22-A114-B JEDEC EIA/JESD22-A114-E	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V Cypress Spec 25-00020	P
Electrostatic Discharge Human Body Model (ESD-HBM) (Special/VCSEL Anode and Cathode bonded out)	2200V JEDEC EIA/JESD22-A114-B JEDEC EIA/JESD22-A114-E	P
High Temperature Operating Life Early Failure Rate (Silicon)	Dynamic Operating Condition, Vcc = 4.2V, 125 C	P
High Temperature Operating Life Early Failure Rate (VCSEL)	Dynamic Operating Condition, Vcc = 4.2V, 40 C	P
High Temperature Operating Life Latent Failure Rate (Silicon)	Dynamic Operating Condition, Vcc = 4.2V, 125 C	P
High Temperature Operating Life Latent Failure Rate (VCSEL)	Dynamic Operating Condition, Vcc = 4.2V, 40 C	P
High Temp Storage	100C	P
Static Latch-up	125C, ± 200mA Cypress Spec 01-00081	P
Temperature Cycle	-40°C to 85C Precondition: JESD22 Moisture Sensitivity MSL3 192 Hrs 30°C/60%RH+3IR-Reflow, 260°C+0, -5°C	P
Temperature Humidity Bias	85C, 85%RH Precondition: JESD22 Moisture Sensitivity MSL3 192 Hrs 30°C/60%RH+3IR-Reflow, 260°C+0, -5°C	P
Wafer Level Data Retention	250C	P
Assy Bond Pull	Cypress Spec 12-00292	P
Die Shear	Cypress Spec 12-00292	P
External Visual	Cypress Spec 12-00292	P
Internal Visual	Cypress Spec 25-00017	P
Mechanical Shock	JEDEC JESD22-B104	P
Mechanical Vibration	JEDEC JESD22-B103	P
Physical Dimension	Cypress Spec 25-00031	P
Solderability	Cypress Spec 25-00018	P
X-Ray	Cypress Spec 12-00292	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF ³	Failure Rate
High Temperature Operating Life Early Failure Rate (Silicon)	1,963 Devices	1	N/A	N/A	509 PPM
High Temperature Operating Life Early Failure Rate (VCSEL)	2, 988 Devices	0	N/A	N/A	0 PPM
High Temperature Operating Life ^{1,2,3} Long Term Failure Rate (Silicon)	9,705,903	0	0.7eV	147	.0094% / 1K hrs
High Temperature Operating Life ^{2,3,4} Long Term Failure Rate (VCSEL)	1,596,995	0	0.7eV	4	.0574% / 1K hrs

- ¹ For Silicon Assuming an ambient temperature of 45°C and a junction temperature rise of 5°C.
² Chi-squared 60% estimations used to calculate the failure rate.
³ Thermal Acceleration Factor is calculated from the Arrhenius equation
⁴ For VCSEL Assuming an ambient temperature of 25°C and a junction temperature rise of 5°C.

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A =The Activation Energy of the defect mechanism.
 K = Boltzmann's constant = 8.62x10⁻⁵ eV/Kelvin.
 T₁ is the junction temperature of the device under stress and T₂ is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #: 071502

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: BOND PULL							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	5	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	5	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	5	0	
STRESS: DATA RETENTION, WAFER LEVEL 250C							
CYONS1001 (7CN1001A)	2613676			5	257	0	
STRESS: DIE SHEAR							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	15	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	15	0	
CYONS1001L (7CN1001AT)	N/A	N/A	CML-R	COMP	15	0	
STRESS: ELECTROSTATIC DISCHARGE HUMAN BODY MODEL PER JEDEC EIA/JESD22-A114-B)							
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	1100V	3	0	
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	2200V	9	0	
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	3300V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	1100V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	2200V	9	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	3300V	3	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	1100V	3	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	2200V	9	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	3300V	3	0	
STRESS: ELECTROSTATIC DISCHARGE CHARGE DEVICE MODEL							
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	200V	3	0	
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	500V	9	0	
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	750V	3	0	
CYONS1001 (7CN100AT)	2602074	610626811	CML-R	1000V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	200V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	500V	9	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	750V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	1000V	3	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	200V	3	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	500V	9	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	750V	3	0	
CYONS1001 (7CN100AT)	2602074	610632941	CML-R	1000V	3	0	

Reliability Test Data

QTP #: 071502

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ELECTROSTATIC DISCHARGE HUMAN BODY MODEL PER JEDEC EIA/JESD22-A114-B (Special VCSEL)							
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	1100V	3	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	2200V	9	0	
CYONS1001 (7CN100AT)	2602074	610632280	CML-R	3300V	3	0	
STRESS: EXTERNAL VISUAL							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	25	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	25	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	25	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 125C, 4.2V, Vcc Max							
CYONS1001L (7CN1001AT)	2613673	610716161	CML-R	72	339	0	
CYONS1001L (7CN1001AT)	2628786	610718715	CML-R	72	332	1	(Bin6, Non-visual
CYONS1001L (7CN1001AT)	2632383	610721350	CML-R	72	337	0	from VCSEL EFR/LFR)
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 40C, 4.2V, Vcc Max(VCSEL)							
CYONS1001L (7CN1001AT)	2613673	610716161	CML-R	168	1009	0	
CYONS1001L (7CN1001AT)	2628786	610718715	CML-R	168	989	0	
CYONS1001L (7CN1001AT)	2632383	610721350	CML-R	168	990	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 125C, 4.2V, Vcc Max							
CYONS1001 (7CN1001AT)	2613673	610716161	CML-R	180	228	0	
CYONS1001 (7CN1001AT)	2613673	610716161	CML-R	300	220	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 40C, 4.2V, Vcc Max(VCSEL)							
CYONS1001 (7CN1001AT)	2613673	610716161	CML-R	336	227	0	
CYONS1001 (7CN1001AT)	2613673	610716161	CML-R	650	227	0	
CYONS1001L (7CN1001AT)	2628786	610718715	CML-R	336	233	0	
CYONS1001L (7CN1001AT)	2628786	610718715	CML-R	650	232	0	
CYONS1001L (7CN1001AT)	2632383	610721350	CML-R	336	235	0	
CYONS1001L (7CN1001AT)	2632383	610721350	CML-R	650	235	0	
STRESS: HIGH TEMP STORAGE							
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	500	45	0	
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	1000	45	0	

Reliability Test Data

QTP #: 071502

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: INTERNAL VISUAL							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	5	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	5	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	5	0	
STRESS: MECHANICAL SHOCK PER JESD22-B104							
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	COMP	17	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	15	0	
STRESS: MECHANICAL VIBRATION PER JESD22-B103							
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	COMP	17	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	15	0	
STRESS: PHYSICAL DIMENSIONS							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	10	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	10	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	10	0	
STRESS: SOLDERABILITY							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	3	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	3	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	3	0	
STRESS: STATIC LATCH-UP 125C, ± 200mA							
CYONS1001 (7CN1001AT)	2602074	610626811	CML-R	COMP	3	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	3	0	
CYONS1001 (7CN1001AT)	2630056	610703842	CML-R	COMP	3	0	
STRESS: TC COND. -40C TO 85 C, PRECONDITION 192 HRS 30C/60%RH, MSL3							
CYONS1001 (7CN1001AT)	2602074	610626811	CML-R	300	45	0	
CYONS1001 (7CN1001AT)	2602074	610626811	CML-R	500	45	0	
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	300	45	0	
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	500	45	0	
CYONS1001 (7CN1001AT)	2602074	610632941	CML-R	300	45	0	
CYONS1001 (7CN1001AT)	2602074	610632941	CML-R	500	44	0	

Reliability Test Data

QTP #: 071502

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: TEMP HUMIDITY BIAS, PRECONDITION 192 HRS 30C/60%RH, MSL3							
CYONS1001 (7CN1001AT)	2602074	610626811	CML-R	168	45	0	
CYONS1001 (7CN1001AT)	2602074	610322280	CML-R	168	45	0	
STRESS: X-RAY							
CYONS1001L (7CN1001AT)	2630056	610703642	CML-R	COMP	15	0	
CYONS1001L (7CN1001AT)	2631220	610703184	CML-R	COMP	15	0	
CYONS1001L (7CN1001AT)	2631220		CML-R	COMP	15	0	

Reliability Test Data

QTP #: 072206

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: ELECTROSTATIC DISCHARGE HUMAN BODY MODEL PER JEDEC EIA/JESD22-A114-E)							
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	1100V	3	0	
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	2200V	8	0	
CYONS10820 (7CN1002AT))	4634005	610725319	CML-R	3300V	3	0	
STRESS: ELECTROSTATIC DISCHARGE CHARGE DEVICE MODEL							
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	500V	9	0	
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	750V	3	0	
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	1000V	3	0	
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	1250V	3	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 125C, 4.2V, Vcc Max							
CYONS1001L (7CN1001AT)	2631219	610729933	CML-R	72	955	0	
STRESS: STATIC LATCH-UP 125C, ± 200mA							
CYONS10820 (7CN1002AT)	4634005	610725319	CML-R	COMP	3	0	